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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	625
Number of Logic Elements/Cells	5000
Total RAM Bits	169984
Number of I/O	172
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-5e-7ftn256c

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# LatticeXP2 Family Data Sheet Introduction

#### February 2012

## Features

- flexiFLASH<sup>™</sup> Architecture
  - Instant-on
  - Infinitely reconfigurable
  - Single chip
  - FlashBAK<sup>™</sup> technology
  - Serial TAG memory
  - Design security

#### Live Update Technology

- TransFR<sup>™</sup> technology
- Secure updates with 128 bit AES encryption
- Dual-boot with external SPI

#### ■ sysDSP<sup>™</sup> Block

- Three to eight blocks for high performance Multiply and Accumulate
- 12 to 32 18x18 multipliers
- Each block supports one 36x36 multiplier or four 18x18 or eight 9x9 multipliers

### Embedded and Distributed Memory

- Up to 885 Kbits sysMEM<sup>™</sup> EBR
- Up to 83 Kbits Distributed RAM

#### ■ sysCLOCK<sup>™</sup> PLLs

- Up to four analog PLLs per device
- Clock multiply, divide and phase shifting

## Flexible I/O Buffer

- sysIO<sup>™</sup> buffer supports:
  - LVCMOS 33/25/18/15/12; LVTTL
  - SSTL 33/25/18 class I, II
  - HSTL15 class I; HSTL18 class I, II
  - PCI
  - LVDS, Bus-LVDS, MLVDS, LVPECL, RSDS
- Pre-engineered Source Synchronous Interfaces
  - DDR / DDR2 interfaces up to 200 MHz
  - 7:1 LVDS interfaces support display applications
  - XGMII
- Density And Package Options
  - 5k to 40k LUT4s, 86 to 540 I/Os
  - csBGA, TQFP, PQFP, ftBGA and fpBGA packages
  - Density migration supported
- Flexible Device Configuration
  - SPI (master and slave) Boot Flash Interface
  - Dual Boot Image supported
  - Soft Error Detect (SED) macro embedded

### System Level Support

- IEEE 1149.1 and IEEE 1532 Compliant
- · On-chip oscillator for initialization & general use
- Devices operate with 1.2V power supply

Device	XP2-5	XP2-8	XP2-17	XP2-30	XP2-40
LUTs (K)	5	8	17	29	40
Distributed RAM (KBits)	10	18	35	56	83
EBR SRAM (KBits)	166	221	276	387	885
EBR SRAM Blocks	9	12	15	21	48
sysDSP Blocks	3	4	5	7	8
18 x 18 Multipliers	12	16	20	28	32
V <sub>CC</sub> Voltage	1.2	1.2	1.2	1.2	1.2
GPLL	2	2	4	4	4
Max Available I/O	172	201	358	472	540
Packages and I/O Combinations					•
132-Ball csBGA (8 x 8 mm)	86	86			
144-Pin TQFP (20 x 20 mm)	100	100			
208-Pin PQFP (28 x 28 mm)	146	146	146		
256-Ball ftBGA (17 x17 mm)	172	201	201	201	
484-Ball fpBGA (23 x 23 mm)			358	363	363
672-Ball fpBGA (27 x 27 mm)				472	540

### Table 1-1. LatticeXP2 Family Selection Guide

### Data Sheet DS1009

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### Figure 2-2. PFU Diagram



### Slice

Slice 0 through Slice 2 contain two 4-input combinatorial Look-Up Tables (LUT4), which feed two registers. Slice 3 contains two LUT4s and no registers. For PFUs, Slice 0 and Slice 2 can also be configured as distributed memory, a capability not available in PFF blocks. Table 2-1 shows the capability of the slices in both PFF and PFU blocks along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. There is control logic to perform set/reset functions (programmable as synchronous/asynchronous), clock select, chip-select and wider RAM/ROM functions. Figure 2-3 shows an overview of the internal logic of the slice. The registers in the slice can be configured as positive/negative edge triggered or level sensitive clocks.

Table 2-1.	Resources	and Modes	Available	per Slice
			/ IT amaint	

	PFU E	BLock	PFF Block		
Slice	Resources	Modes	Resources	Modes	
Slice 0	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM	
Slice 1	2 LUT4s and 2 Registers	Logic, Ripple, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM	
Slice 2	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM	
Slice 3	2 LUT4s	Logic, ROM	2 LUT4s	Logic, ROM	

Slice 0 through Slice 2 have 14 input signals: 13 signals from routing and one from the carry-chain (from the adjacent slice or PFU). There are seven outputs: six to routing and one to carry-chain (to the adjacent PFU). Slice 3 has 13 input signals from routing and four signals to routing. Table 2-2 lists the signals associated with Slice 0 to Slice 2.



### Figure 2-16. FlashBAK Technology



## **Memory Cascading**

Larger and deeper blocks of RAMs can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

### Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

EBR memory supports two forms of write behavior for single port or dual port operation:

- 1. Normal Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- 2. Write Through A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.

### **Memory Core Reset**

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B respectively. GSRN, the global reset signal, resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-17.

Figure 2-17. Memory Core Reset





## **MULTADDSUB sysDSP Element**

In this case, the operands A0 and B0 are multiplied and the result is added/subtracted with the result of the multiplier operation of operands A1 and B1. The user can enable the input, output and pipeline registers. Figure 2-22 shows the MULTADDSUB sysDSP element.

### Figure 2-22. MULTADDSUB





#### Table 2-11. PIO Signal List

Name	Туре	Description
CE	Control from the core	Clock enables for input and output block flip-flops
CLK	Control from the core	System clocks for input and output blocks
ECLK1, ECLK2	Control from the core	Fast edge clocks
LSR	Control from the core	Local Set/Reset
GSRN	Control from routing	Global Set/Reset (active low)
INCK <sup>2</sup>	Input to the core	Input to Primary Clock Network or PLL reference inputs
DQS	Input to PIO	DQS signal from logic (routing) to PIO
INDD	Input to the core	Unregistered data input to core
INFF	Input to the core	Registered input on positive edge of the clock (CLK0)
IPOS0, IPOS1	Input to the core	Double data rate registered inputs to the core
QPOS0 <sup>1</sup> , QPOS1 <sup>1</sup>	Input to the core	Gearbox pipelined inputs to the core
QNEG0 <sup>1</sup> , QNEG1 <sup>1</sup>	Input to the core	Gearbox pipelined inputs to the core
OPOS0, ONEG0, OPOS2, ONEG2	Output data from the core	Output signals from the core for SDR and DDR operation
OPOS1 ONEG1	Tristate control from the core	Signals to Tristate Register block for DDR operation
DEL[3:0]	Control from the core	Dynamic input delay control bits
TD	Tristate control from the core	Tristate signal from the core used in SDR operation
DDRCLKPOL	Control from clock polarity bus	Controls the polarity of the clock (CLK0) that feed the DDR input block
DQSXFER	Control from core	Controls signal to the Output block

1. Signals available on left/right/bottom only.

2. Selected I/O.

## PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with necessary clock and selection logic.

### Input Register Block

The input register blocks for PIOs contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-26 shows the diagram of the input register block.

Input signals are fed from the sysIO buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In the Single Data Rate (SDR) mode, the data is registered, by one of the registers in the SDR Sync register block, with the system clock. In DDR mode two registers are used to sample the data on the positive and negative edges of the DQS signal which creates two data streams, D0 and D2. D0 and D2 are synchronized with the system clock before entering the core. Further information on this topic can be found in the DDR Memory Support section of this data sheet.

By combining input blocks of the complementary PIOs and sharing registers from output blocks, a gearbox function can be implemented, that takes a double data rate signal applied to PIOA and converts it as four data streams, IPOS0A, IPOS1A, IPOS0B and IPOS1B. Figure 2-26 shows the diagram using this gearbox function. For more information on this topic, please see TN1138, LatticeXP2 High Speed I/O Interface.



The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred from the DQS to system clock domain. For further discussion on this topic, see the DDR Memory section of this data sheet.





## **Output Register Block**

The output register block provides the ability to register signals from the core of the device before they are passed to the sysIO buffers. The blocks on the PIOs on the left, right and bottom contain registers for SDR operation that are combined with an additional latch for DDR operation. Figure 2-27 shows the diagram of the Output Register Block for PIOs.

In SDR mode, ONEG0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a Dtype or latch. In DDR mode, ONEG0 and OPOS0 are fed into registers on the positive edge of the clock. At the next clock cycle the registered OPOS0 is latched. A multiplexer running off the same clock cycle selects the correct register to feed the output (D0).

By combining output blocks of the complementary PIOs and sharing some registers from input blocks, a gearbox function can be implemented, to take four data streams ONEG0A, ONEG1A, ONEG1B and ONEG1B. Figure 2-27



### Tristate Register Block

The tristate register block provides the ability to register tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation and an additional latch for DDR operation. Figure 2-27 shows the Tristate Register Block with the Output Block

In SDR mode, ONEG1 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as Dtype or latch. In DDR mode, ONEG1 and OPOS1 are fed into registers on the positive edge of the clock. Then in the next clock the registered OPOS1 is latched. A multiplexer running off the same clock cycle selects the correct register for feeding to the output (D0).

### **Control Logic Block**

The control logic block allows the selection and modification of control signals for use in the PIO block. A clock signal is selected from general purpose routing, ECLK1, ECLK2 or a DQS signal (from the programmable DQS pin) and is provided to the input register block. The clock can optionally be inverted.

## **DDR Memory Support**

PICs have additional circuitry to allow implementation of high speed source synchronous and DDR memory interfaces.

PICs have registered elements that support DDR memory interfaces. Interfaces on the left and right edges are designed for DDR memories that support 16 bits of data, whereas interfaces on the top and bottom are designed for memories that support 18 bits of data. One of every 16 PIOs on the left and right and one of every 18 PIOs on the top and bottom contain delay elements to facilitate the generation of DQS signals. The DQS signals feed the DQS buses which span the set of 16 or 18 PIOs. Figure 2-28 and Figure 2-29 show the DQS pin assignments in each set of PIOs.

The exact DQS pins are shown in a dual function in the Logic Signal Connections table in this data sheet. Additional detail is provided in the Signal Descriptions table. The DQS signal from the bus is used to strobe the DDR data from the memory into input register blocks. For additional information on using DDR memory support please see TN1138, <u>LatticeXP2 High Speed I/O Interface</u>.



#### Table 2-13. Supported Output Standards

Output Standard Drive		V <sub>CCIO</sub> (Nom.)		
Single-ended Interfaces				
LVTTL	4mA, 8mA, 12mA, 16mA, 20mA	3.3		
LVCMOS33	4mA, 8mA, 12mA 16mA, 20mA	3.3		
LVCMOS25	4mA, 8mA, 12mA, 16mA, 20mA	2.5		
LVCMOS18	4mA, 8mA, 12mA, 16mA	1.8		
LVCMOS15	4mA, 8mA	1.5		
LVCMOS12	2mA, 6mA	1.2		
LVCMOS33, Open Drain	4mA, 8mA, 12mA 16mA, 20mA	—		
LVCMOS25, Open Drain	4mA, 8mA, 12mA 16mA, 20mA			
LVCMOS18, Open Drain	4mA, 8mA, 12mA 16mA			
LVCMOS15, Open Drain	4mA, 8mA	_		
LVCMOS12, Open Drain	2mA, 6mA	_		
PCI33	N/A	3.3		
HSTL18 Class I, II	N/A	1.8		
HSTL15 Class I	N/A	1.5		
SSTL33 Class I, II	N/A	3.3		
SSTL25 Class I, II	N/A	2.5		
SSTL18 Class I, II	N/A	1.8		
Differential Interfaces				
Differential SSTL33, Class I, II	N/A	3.3		
Differential SSTL25, Class I, II	N/A	2.5		
Differential SSTL18, Class I, II	N/A	1.8		
Differential HSTL18, Class I, II	N/A	1.8		
Differential HSTL15, Class I	N/A	1.5		
LVDS <sup>1, 2</sup>	N/A	2.5		
MLVDS <sup>1</sup>	N/A	2.5		
BLVDS <sup>1</sup>	N/A	2.5		
LVPECL <sup>1</sup>	N/A	3.3		
RSDS <sup>1</sup>	N/A	2.5		
LVCMOS33D <sup>1</sup>	4mA, 8mA, 12mA, 16mA, 20mA	3.3		

1. Emulated with external resistors.

2. On the left and right edges, LVDS outputs are supported with a dedicated differential output driver on 50% of the I/Os. This solution does not require external resistors at the driver.

## **Hot Socketing**

LatticeXP2 devices have been carefully designed to ensure predictable behavior during power-up and powerdown. Power supplies can be sequenced in any order. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled to within specified limits. This allows for easy integration with the rest of the system. These capabilities make the LatticeXP2 ideal for many multiple power supply and hot-swap applications.

## IEEE 1149.1-Compliant Boundary Scan Testability

All LatticeXP2 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant Test Access Port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in



# Programming and Erase Flash Supply Current<sup>1, 2, 3, 4, 5</sup>

### **Over Recommended Operating Conditions**

Symbol	Parameter	Device	Typical (25°C, Max. Supply) <sup>6</sup>	Units
		XP2-5	17	mA
		XP2-8	21	mA
I <sub>CC</sub>	Core Power Supply Current	XP2-17	28	mA
		XP2-30	36	mA
		XP2-40	50	mA
I <sub>CCAUX</sub>		XP2-5	64	mA
	Auxiliary Power Supply Current <sup>7</sup>	XP2-8	66	mA
		XP2-17	83	mA
		XP2-30	87	mA
		XP2-40	88	mA
I <sub>CCPLL</sub>	PLL Power Supply Current (per PLL)		0.1	mA
I <sub>CCIO</sub>	Bank Power Supply Current (per Bank)		5	mA
I <sub>CCJ</sub>	V <sub>CCJ</sub> Power Supply Current <sup>8</sup>		14	mA

1. For further information on supply current, please see TN1139, Power Estimation and Management for LatticeXP2 Devices.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V<sub>CCIO</sub> or GND.

3. Frequency 0 MHz (excludes dynamic power from FPGA operation).

4. A specific configuration pattern is used that scales with the size of the device; consists of 75% PFU utilization, 50% EBR, and 25% I/O configuration.

5. Bypass or decoupling capacitor across the supply.

6.  $T_J = 25^{\circ}C$ , power supplies at nominal voltage.

 In fpBGA and ftBGA packages the PLLs are connected to and powered from the auxiliary power supply. For these packages, the actual auxiliary supply current is the sum of I<sub>CCAUX</sub> and I<sub>CCPLL</sub>. For csBGA, PQFP and TQFP packages the PLLs are powered independent of the auxiliary power supply.

8. When programming via JTAG.



## BLVDS

The LatticeXP2 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.





#### Table 3-2. BLVDS DC Conditions<sup>1</sup>

		Typical		
Parameter	Description	<b>Ζο = 45</b> Ω	<b>Ζο = 90</b> Ω	Units
V <sub>CCIO</sub>	Output Driver Supply (+/- 5%)	2.50	2.50	V
Z <sub>OUT</sub>	Driver Impedance	10.00	10.00	Ω
R <sub>S</sub>	Driver Series Resistor (+/- 1%)	90.00	90.00	Ω
R <sub>TL</sub>	Driver Parallel Resistor (+/- 1%)	45.00	90.00	Ω
R <sub>TR</sub>	Receiver Termination (+/- 1%)	45.00	90.00	Ω
V <sub>OH</sub>	Output High Voltage (After R <sub>TL</sub> )	1.38	1.48	V
V <sub>OL</sub>	Output Low Voltage (After R <sub>TL</sub> )	1.12	1.02	V
V <sub>OD</sub>	Output Differential Voltage (After R <sub>TL</sub> )	0.25	0.46	V
V <sub>CM</sub>	Output Common Mode Voltage	1.25	1.25	V
I <sub>DC</sub>	DC Output Current	11.24	10.20	mA

**Over Recommended Operating Conditions** 

1. For input buffer, see LVDS table.



## **Register-to-Register Performance (Continued)**

Function	-7 Timing	Units
DSP IP Functions		
16-Tap Fully-Parallel FIR Filter	198	MHz
1024-pt FFT	221	MHz
8X8 Matrix Multiplication	196	MHz

1. These timing numbers were generated using the ispLEVER design tool. Exact performance may vary with device, design and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

## **Derating Timing Tables**

Logic timing provided in the following sections of this data sheet and the Diamond design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond design tool can provide logic timing numbers at a particular temperature and voltage.



# LatticeXP2 Family Timing Adders<sup>1, 2, 3, 4</sup> (Continued)

Buffer Type	Description	-7	-6	-5	Units
HSTL15_I	HSTL_15 class I 4mA drive	0.32	0.69	1.06	ns
HSTL15D_I	Differential HSTL 15 class I 4mA drive	0.32	0.69	1.06	ns
SSTL33_I	SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33_II	SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL33D_I	Differential SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33D_II	Differential SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL25_I	SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25_II	SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL25D_I	Differential SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25D_II	Differential SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL18_I	SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18_II	SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
SSTL18D_I	Differential SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18D_II	Differential SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
LVTTL33_4mA	LVTTL 4mA drive	-0.37	-0.05	0.26	ns
LVTTL33_8mA	LVTTL 8mA drive	-0.45	-0.18	0.10	ns
LVTTL33_12mA	LVTTL 12mA drive	-0.52	-0.24	0.04	ns
LVTTL33_16mA	LVTTL 16mA drive	-0.43	-0.14	0.14	ns
LVTTL33_20mA	LVTTL 20mA drive	-0.46	-0.18	0.09	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, fast slew rate	-0.37	-0.05	0.26	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, fast slew rate	-0.45	-0.18	0.10	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, fast slew rate	-0.52	-0.24	0.04	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, fast slew rate	-0.43	-0.14	0.14	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, fast slew rate	-0.46	-0.18	0.09	ns
LVCMOS25_4mA	LVCMOS 2.5 4mA drive, fast slew rate	-0.42	-0.15	0.13	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive, fast slew rate	-0.48	-0.21	0.05	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive, fast slew rate	0.00	0.00	0.00	ns
LVCMOS25_16mA	LVCMOS 2.5 16mA drive, fast slew rate	-0.45	-0.18	0.08	ns
LVCMOS25_20mA	LVCMOS 2.5 20mA drive, fast slew rate	-0.49	-0.22	0.04	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive, fast slew rate	-0.46	-0.18	0.10	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive, fast slew rate	-0.52	-0.25	0.02	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive, fast slew rate	-0.56	-0.30	-0.03	ns
LVCMOS18_16mA	LVCMOS 1.8 16mA drive, fast slew rate	-0.50	-0.24	0.03	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive, fast slew rate	-0.45	-0.17	0.11	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive, fast slew rate	-0.53	-0.26	0.00	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive, fast slew rate	-0.46	-0.19	0.08	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive, fast slew rate	-0.55	-0.29	-0.02	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, slow slew rate	0.98	1.41	1.84	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, slow slew rate	0.74	1.16	1.58	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, slow slew rate	0.56	0.97	1.38	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, slow slew rate	0.77	1.19	1.61	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, slow slew rate	0.57	0.98	1.40	ns

## **Over Recommended Operating Conditions**



## LatticeXP2 sysCONFIG Port Timing Specifications

Parameter	Description	Min	Max	Units			
sysCONFIG PO	sysCONFIG POR, Initialization and Wake Up						
t <sub>ICFG</sub>	Minimum Vcc to INITN High	_	50	ms			
t <sub>VMC</sub>	Time from t <sub>ICFG</sub> to valid Master CCLK	_	2	μs			
t <sub>PRGMRJ</sub>	PROGRAMN Pin Pulse Rejection	_	12	ns			
t <sub>PRGM</sub>	PROGRAMN Low Time to Start Configuration	50	—	ns			
t <sub>DINIT</sub> 1	PROGRAMN High to INITN High Delay	_	1	ms			
t <sub>DPPINIT</sub>	Delay Time from PROGRAMN Low to INITN Low	_	50	ns			
t <sub>DPPDONE</sub>	Delay Time from PROGRAMN Low to DONE Low	_	50	ns			
t <sub>IODISS</sub>	User I/O Disable from PROGRAMN Low	_	35	ns			
t <sub>IOENSS</sub>	User I/O Enabled Time from CCLK Edge During Wake-up Sequence	_	25	ns			
t <sub>MWC</sub>	Additional Wake Master Clock Signals after DONE Pin High	0	—	Cycles			
sysCONFIG SP	I Port (Master)						
t <sub>CFGX</sub>	INITN High to CCLK Low	_	1	μs			
t <sub>CSSPI</sub>	INITN High to CSSPIN Low	_	2	μs			
t <sub>CSCCLK</sub>	CCLK Low before CSSPIN Low	0	—	ns			
t <sub>SOCDO</sub>	CCLK Low to Output Valid	_	15	ns			
t <sub>CSPID</sub>	CSSPIN[0:1] Low to First CCLK Edge Setup Time	2cyc	600+6cyc	ns			
f <sub>MAXSPI</sub>	Max CCLK Frequency	—	20	MHz			
t <sub>SUSPI</sub>	SOSPI Data Setup Time Before CCLK	7	—	ns			
t <sub>HSPI</sub>	SOSPI Data Hold Time After CCLK	10	—	ns			
sysCONFIG SP	I Port (Slave)						
f <sub>MAXSPIS</sub>	Slave CCLK Frequency	—	25	MHz			
t <sub>RF</sub>	Rise and Fall Time	50	—	mV/ns			
t <sub>STCO</sub>	Falling Edge of CCLK to SOSPI Active	—	20	ns			
t <sub>STOZ</sub>	Falling Edge of CCLK to SOSPI Disable	—	20	ns			
t <sub>STSU</sub>	Data Setup Time (SISPI)	8	—	ns			
t <sub>STH</sub>	Data Hold Time (SISPI)	10	—	ns			
t <sub>sтскн</sub>	CCLK Clock Pulse Width, High	0.02	200	μs			
t <sub>STCKL</sub>	CCLK Clock Pulse Width, Low	0.02	200	μs			
t <sub>STVO</sub>	Falling Edge of CCLK to Valid SOSPI Output		20	ns			
t <sub>SCS</sub>	CSSPISN High Time	25	—	ns			
t <sub>SCSS</sub>	CSSPISN Setup Time	25	—	ns			
t <sub>SCSH</sub>	CSSPISN Hold Time	25	—	ns			

### **Over Recommended Operating Conditions**

1. Re-toggling the PROGRAMN pin is not permitted until the INITN pin is high. Avoid consecutive toggling of PROGRAMN.



# On-Chip Oscillator and Configuration Master Clock Characteristics

Parameter	Min.	Max.	Units
Master Clock Frequency	Selected value -30%	Selected value +30%	MHz
Duty Cycle	40	60	%

### **Over Recommended Operating Conditions**

### Figure 3-9. Master SPI Configuration Waveforms





## FlashBAK Time (from EBR to Flash)

### **Over Recommended Operating Conditions**

Device	EBR Density (Bits)	Time (Typ.)	Units
XP2-5	166K	1.5	S
XP2-8	221K	1.5	S
XP2-17	276K	1.5	S
XP2-30	387K	2.0	S
XP2-40	885K	3.0	S

## JTAG Port Timing Specifications

### **Over Recommended Operating Conditions**

Symbol	Parameter	Min.	Max.	Units
f <sub>MAX</sub>	TCK Clock Frequency	—	25	MHz
t <sub>BTCP</sub>	TCK [BSCAN] clock pulse width	40	—	ns
t <sub>BTCPH</sub>	TCK [BSCAN] clock pulse width high	20	—	ns
t <sub>BTCPL</sub>	TCK [BSCAN] clock pulse width low	20	—	ns
t <sub>BTS</sub>	TCK [BSCAN] setup time	8	—	ns
t <sub>BTH</sub>	TCK [BSCAN] hold time	10	—	ns
t <sub>BTRF</sub>	TCK [BSCAN] rise/fall time	50	—	mV/ns
t <sub>BTCO</sub>	TAP controller falling edge of clock to valid output	—	10	ns
t <sub>BTCODIS</sub>	TAP controller falling edge of clock to valid disable	—	10	ns
t <sub>BTCOEN</sub>	TAP controller falling edge of clock to valid enable	—	10	ns
t <sub>BTCRS</sub>	BSCAN test capture register setup time	8	—	ns
t <sub>BTCRH</sub>	BSCAN test capture register hold time	25	—	ns
t <sub>BUTCO</sub>	BSCAN test update register, falling edge of clock to valid output	—	25	ns
t <sub>BTUODIS</sub>	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
t <sub>BTUPOEN</sub>	BSCAN test update register, falling edge of clock to valid enable	_	25	ns



## **Switching Test Conditions**

Figure 3-11 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

### Figure 3-11. Output Test Load, LVTTL and LVCMOS Standards



\*CL Includes Test Fixture and Probe Capacitance

 Table 3-6. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R <sub>1</sub>	R <sub>2</sub>	CL	Timing Ref.	V <sub>T</sub>
				LVCMOS 3.3 = 1.5V	
				LVCMOS 2.5 = $V_{CCIO}/2$	
LVTTL and other LVCMOS settings (L -> H, H -> L)	$\infty$	$\infty$	0pF	LVCMOS 1.8 = V <sub>CCIO</sub> /2	
	LVCMOS 1.5 = V <sub>CCIO</sub> /2			LVCMOS 1.5 = $V_{CCIO}/2$	_
				LVCMOS 1.2 = V <sub>CCIO</sub> /2	_
LVCMOS 2.5 I/O (Z -> H)	8	1MΩ		V <sub>CCIO</sub> /2	
LVCMOS 2.5 I/O (Z -> L)	1MΩ	$\infty$		V <sub>CCIO</sub> /2	V <sub>CCIO</sub>
LVCMOS 2.5 I/O (H -> Z)	8	100		V <sub>OH</sub> - 0.10	
LVCMOS 2.5 I/O (L -> Z)	100	$\infty$		V <sub>OL</sub> + 0.10	V <sub>CCIO</sub>

Note: Output test conditions for all other interfaces are determined by the respective standards.



## PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges	of the Device	
D[Edgo] [n 4]	А	DQ
r[Euge] [11-4]	В	DQ
D[Edga] [n 2]	А	DQ
r[Euge] [II-3]	В	DQ
D[Edgo] [n 2]	А	DQ
	В	DQ
P[Edge] [n-1]	А	DQ
	В	DQ
P[Edge] [n]	А	[Edge]DQSn
	В	DQ
P[Edge] [n+1]	А	DQ
	В	DQ
P[Edge] [n+2]	А	DQ
	В	DQ
P[Edge] [n+3]	А	DQ
	В	DQ
For Top and Bottom Edge	es of the Device	
P[Edge] [n-4]	A	DQ
	В	DQ
P[Edge] [n-3]	A	DQ
	В	DQ
P[Edge] [n-2]	A	DQ
. [=090] [ =]	В	DQ
P[Edge] [n-1]	A	DQ
. [=090][]	В	DQ
P[Edge] [n]	A	[Edge]DQSn
. [====================================	В	DQ
P[Edge] [n+1]	A	DQ
. [=a90][]	В	DQ
P[Edge] [n+2]	A	DQ
. [=380][=]	В	DQ
P[Edge] [n+3]	A	DQ
. [=390] [0]	В	DQ
P[Edge] [n+4]	A	DQ
. [=380][]	В	DQ

Notes:

1. "n" is a row PIC number.

<sup>2.</sup> The DDR interface is designed for memories that support one DQS strobe up to 16 bits of data for the left and right edges and up to 18 bits of data for the top and bottom edges. In some packages, all the potential DDR data (DQ) pins may not be available. PIC numbering definitions are provided in the "Signal Names" column of the Signal Descriptions table.



## Pin Information Summary (Cont.)

XP2-5				XP	2-8			XP2-17	,	XP2-30		XP2-40					
Pin Ty	ре	132 csBGA	144 TQFP	208 PQFP	256 ftBGA	132 csBGA	144 TQFP	208 PQFP	256 ftBGA	208 PQFP	256 ftBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA	484 fpBGA	672 fpBGA
	Bank0	18	20	20	26	18	20	20	28	20	28	52	28	52	70	52	70
	Bank1	4	6	18	18	4	6	18	22	18	22	36	22	36	54	36	70
	Bank2	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
PCI capable I/Os	Bank3	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank	Bank4	8	8	18	18	8	8	18	26	18	26	36	26	38	54	38	70
	Bank5	14	18	20	24	14	18	20	24	20	24	52	24	53	70	53	70
	Bank6	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank7	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

1. Minimum requirement to implement a fully functional 8-bit wide DDR bus. Available DDR interface consists of at least 12 I/Os (1 DQS + 1 DQSB + 8 DQs + 1 DM + Bank VREF1).

## **Logic Signal Connections**

Package pinout information can be found under "Data Sheets" on the LatticeXP2 product page of the Lattice website a www.latticesemi.com/products/fpga/xp2 and in the Lattice Diamond design software.

## **Thermal Management**

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Designers must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Lattice <u>Thermal Management</u> document to find the device/ package specific thermal values.

## For Further Information

- TN1139, Power Estimation and Management for LatticeXP2 Devices
- Power Calculator tool is included with the Lattice Diamond design tool or as a standalone download from <a href="http://www.latticesemi.com/products/designsoftware">www.latticesemi.com/products/designsoftware</a>



# Lead-Free Packaging

## Commercial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	5
LFXP2-5E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	5
LFXP2-5E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	5
LFXP2-5E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	5
LFXP2-5E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	5
LFXP2-5E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	5
LFXP2-5E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	5
LFXP2-5E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	5
LFXP2-5E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	5
LFXP2-5E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	5
LFXP2-5E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	5
LFXP2-5E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	8
LFXP2-8E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	8
LFXP2-8E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	8
LFXP2-8E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	8
LFXP2-8E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	8
LFXP2-8E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	8
LFXP2-8E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	8
LFXP2-8E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	8
LFXP2-8E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	8
LFXP2-8E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	8
LFXP2-8E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	8
LFXP2-8E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	8

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	17
LFXP2-17E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	17
LFXP2-17E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	17
LFXP2-17E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	17
LFXP2-17E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	17
LFXP2-17E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	17
LFXP2-17E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	17
LFXP2-17E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	17
LFXP2-17E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	17



Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	17
LFXP2-17E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	17
LFXP2-17E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	17
LFXP2-17E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	17
LFXP2-17E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	17
LFXP2-17E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	30
LFXP2-30E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	30
LFXP2-30E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	30
LFXP2-30E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	30
LFXP2-30E-5FN672I	1.2V	-5	Lead-Free fpBGA	672	IND	30
LFXP2-30E-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	30

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	40
LFXP2-40E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	40
LFXP2-40E-5FN672I	1.2V	-5	Lead-Free fpBGA	672	IND	40
LFXP2-40E-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	40